

Notice of References Cited	Application/Control No. 10/700,466	Applicant(s)/Patent Under Reexamination OHMI, TADAHIRO	
	Examiner Thien F. Tran	Art Unit 2811	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Hirayama et al., "Low Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", IEDM Tech. Dig. p249-252, (1999)
	V	
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	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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